# Investigation of BaTiO<sub>3</sub>-NiO composite as compact Dielectric Resonator Antenna

Prithwiraj Ganguly<sup>a</sup>, Vince Kumar<sup>b</sup>, P. Maneesha<sup>a</sup>, Saptarshi Ghosh<sup>c</sup>, Somaditya Sen<sup>a</sup>\*

<sup>a</sup>Department of Physics, Indian Institute of Technology Indore, 453552, India

<sup>b</sup> Department of Physics, Deenbandhu Chhotu Ram University of Science and Technology, Murthal, 131039, Sonepat, Haryana, India

<sup>c</sup>Department of Electrical engineering, Indian Institute of Technology Indore, 453552, India

\*Corresponding author; sens@iiti.ac.in

#### Abstract

A compact dielectric resonator antenna has been fabricated on a microstrip transmission line for the purpose of C-band wireless communication using a ceramic material made out of a sintered mixture of BTO and NiO. The antenna parameters are optimized using Ansys HFSS software and verified experimentally. Ni replaces both Ba at A site and Ti at B site. Such a solid solution has a limit depending on the amount of NiO provided during sintering. A complete study of the structural changes and the dielectric constant enables the correlation with the resonating property. All the samples retain the ferroelectric tetragonal *P4mm* phase with a nominal decrease in the c/a ratio. NiO incorporation in BTO decreases the sintering temperature and shows two types of morphology associated with BTO-like and NiO-like phases. It induces prominent reduction in the permittivity and loss tangent (<0.01) in the range 100Hz to 1MHz. These properties make these samples suitable for DRA application in the C-Band range [4-8 GHz]. Experimental and theoretical assessment using HFSS software yields a C-band signal at ~7.27 GHz.

## Introduction:

The significance of semiconductors had been amplified due to the ability to manipulate their conductivity and dielectric properties. Dielectric Resonator Antenna (DRA) is a best example for versatility in the application of dielectric material by modifying the properties of the material for enabling adjustments to the radiation parameters. DRAs have benefits of reduced proximity detuning (for some modes), increased impedance bandwidth, low cost, excellent radiation efficiency, and compactness [1][2]. Unlike microstrip antennas, DRAs do not support surface waves, lowers conductive loss in high frequency domains [Ref]. Since the first original work by

Long at al.[3], many researchers have well explored the different aspects of DRA. The current research aligns with the broader goal of optimizing antenna design by tailoring materials at the microstructural level. Cylindrical DRA (CDRA) is one of the simple DRA designs for tuning the DRA parameters.

The cylindrical DR offers three fundamental modes, HEM<sub>11δ</sub>, TM<sub>01δ</sub> and TE<sub>01δ</sub>[15]. Here the first index denotes the number of full-period field variations in azimuthal direction, second one represents the no. of radial variations and the third index represents the variation in the z-direction [ref]. The resonance frequency of the Higher order mode HEM<sub>11δ</sub> is given by[1];

$$f = \frac{6.324 c}{2\Pi a \sqrt{\epsilon_r + 2}} \left[ 0.27 + 0.36 (\frac{a}{2h}) + 0.002 (\frac{a}{2h})^2 \right]$$

This formula is known to be accurate in the range  $0.4 < \frac{a}{h} < 6$ .

This relation is used to find out the dimension of the CDRA for a particular resonance frequency for  $\text{HEM}_{11\delta}$  mode.

Among the vast range of low loss lead (Pb) free ceramic materials, BaTiO<sub>3</sub> (BTO) based ceramics are mainly utilized for multilayer ceramic capacitors, thermistor, FRAM, piezo-electric sensor for its ferroelectric properties [Ref]. But, for the same reason it has a very high dielectric constant ( $\varepsilon_r$ =120 in GHz range) [Ref]. Though, the size of the DRA is inversely proportional to the  $\varepsilon_r$ , the bandwidth gets minimized for high Q- factor [ref]. Hence, it is required to optimize  $\varepsilon_r$  to have a balance between miniaturization and bandwidth. It is suitable to have the  $\varepsilon_r$  in the range of 20 to 80 [4].

It is reported that Ni doping in BTO decreases the permittivity due to the inhibition of grain growth of BTO with addition of Ni. The A-site doping of BTO decreases the tetragonality and induces a centrosymmetric cubic structure [Fm-3m][5]. However, the B-site doping will induce the hexagonal structure [P6<sub>3</sub>/mmc] of BTO []. Very few studies have employed BTO for DRA applications thus far, like Chandran et. al. used BaTiO<sub>3</sub>/V<sub>2</sub>O<sub>5</sub> composite ( $\varepsilon_r$ =49.3) working at 9.5 GHz while Rejab et. al. [Ref] used Nd-doped BaTiO<sub>3</sub> for X-Band, Suhailrashid.S et al. [Ref] has used BaTiO<sub>3</sub> embedded with TiO<sub>2</sub> nano composite for Wi-Fi applications Nevertheless, as far as the author is aware, no research has been done on the BaTiO<sub>3</sub>-NiO composite for DRA applications. Along with that, different structural characterization techniques (XRD, Raman, FESEM, EDX) have been utilized to gain the understanding of the material properties at the fundamental level and qualify it for DRA.

#### **Experimental techniques:**

BTO-NiO composite (micro powders) had been prepared using commercially available nano-sized particles of BTO and NiO. The molecular weight percentage of NiO in (1-x) BaTiO<sub>3</sub>-(x) NiO varied as x=0, 0.05, 0.1, and 0.15. These samples will be called S0 (x=0), S1 (x=0.05), S2 (x=0.1), and S3 (x=0.15). Stoichiometric combinations of pure BTO and NiO powders were mixed and ground for three hours in an agar mortar. The process ensures the homogeneity of the mixture. The powders of each composition were pressed into three cylindrical pellets of thickness ~1–2 mm and diameter ~10 mm, using a uniaxial hydraulic press (2 tons). Two pellets were prepared with the addition of Polyvinyl Alcohol (PVA) to ensure proper adhesion of the particles. The third pellet was prepared without the addition of PVA to avoid unwanted components from remnants of the PVA. All the pellets were sintered at 1250<sup>o</sup>C for 5 hours with a heating and cooling rate of 5 °C/min. The pellets with PVA were pre-heated at 600 °C for 6 hours to remove the PVA. The sintered pellets for each sample that were pressed without PVA were ground into powder for basic characterizations (XRD and Raman). The PVA-added pellets were used for morphology tests using FESEM. These pellets were also used for dielectric property measurements.

A Bruker D2-Phaser X-Ray Diffractometer has been used to get the X-Ray Diffraction (XRD) data for structural analysis. A Cu K<sub>a</sub> source ( $\lambda =1.54$  Å) at 30 kV and 10 mA is used to take the data at the sweep rate of 0.60 /min within the 20° to 80° range. The phonon modes were studied from room temperature Raman spectroscopy using a Horiba-made LabRAM HR Raman spectrometer (spectral resolution of 0.9 cm<sup>-1</sup>). The illumination source was a He-Ne LASER of wavelength 632.8 nm. A CCD detector is used in backscattered mode along with 600 grating. A Supra55 Zeiss Field Emission Scanning Electron Microscope (FESEM) was used to study the morphology and Energy dispersive X-ray (EDX) data of the sintered pellets. To avoid the charging effect, a metallic gold deposition (~ 5 nm) by sputtering techniques was required for charge drainage from the surface.

The same sintered pellets were used to estimate the dielectric properties of all the samples. Silver electrodes were painted using silver paste on both sides of the pellets for the dielectric measurements. Curing of the silver electrodes was performed at 550 °C for 30 minutes to ensure proper adhesion of the Ag to the pellet surface. A broadband (100 Hz to 1 MHz) Newton's 4th Ltd. dielectric spectrometer was used for the dielectric measurement. The spectrometer is equipped

with a phase sensitive multimeter having signal strength 1 V rms. All measurements are conducted at room temperature.

The antenna design was simulated with ANSYS High Frequency Structure Simulator (HFSS) software. It uses Finite Element Method (FEM) to solve electro-magnetic equations for 3D structures working at high frequency range (micrometer or millimeter wavelength). All the design parameters were optimized using HFSS. The DRA and the microstrip were fabricated with the simulated parameters. The microstrip was fabricated with the help of a 3D printer (LPKF Protomat-S104). A Vector Network Analyzer (VNA) (Amritsu S820E) was used to measure the S<sub>11</sub> parameter.

#### **XRD** analysis:

XRD measurement of all the samples are shown in Figure 1. All the samples reveal a majority phase of the tetragonal *P4mm* space group of BaTiO<sub>3</sub> [Figure 1]. The NiO revealed a cubic [*Fm-3m*] phase. The samples exhibited well defined sharp peaks confirming a crystalline nature of the samples. The intensity of the NiO peaks is found to increase from S2 to S3, which confirms the formation of composite in these samples. Some very small non-stoichiometric impurity peaks are observed in the 27- 31 20 range in all the samples corresponding to Ba<sub>2</sub>TiO<sub>4</sub>, Ba<sub>4</sub>Ti<sub>12</sub>O<sub>7</sub>, Ba<sub>2</sub>Ti<sub>2</sub>O<sub>5</sub>, Ba<sub>6</sub>Ti<sub>17</sub>O<sub>40</sub> phases[6]. These peaks are the result of increase in non-stoichiometry of Ba and Ti in BaTiO<sub>3</sub> lattice due to doping of Ni.



Figure 1 : (a) X-Ray diffraction plot of different samples [BTO peaks(\*) and NiO peaks (#)]. (b) Zoomed image of the highest intensity (100) peak. (c) Zoomed image of the (200) peak.

In ABO<sub>3</sub> perovskite structure, the BO<sub>6</sub> octahedra plays the primary role for ferroelectricity or polarization. In the tetragonal phase of BaTiO<sub>3</sub>, the central Ti ion does not remain at the center of the TiO<sub>6</sub> octahedra, leading to an offset of positive and negative charge center. This in return gives rise to a macroscopic spontaneous polarization P<sub>s</sub> along the [001], resulting in ferroelectricity. Movement of Ti towards the centrosymmetric position leads to the cubic crystal structure and reduction of P<sub>s</sub>. The splitting of two peaks (002) at ~44.9° and (200) at ~ 45.4° confirmed the non-centrosymmetric tetragonal phase of BaTiO<sub>3</sub> [Figure 1(c)]. The highest intensity was of the (110) plane at ~  $31.52^{\circ}$  representing a preferred crystallinity in this orientation for all the fabricated polycrystalline BTO. Slight asymmetry was observed for the (110) plane indicating the tetragonality of these samples [Figure 1b][7]. Two possibilities emerged due to the addition of NiO to BaTiO<sub>3</sub>: (a) Ni doping in BaTiO<sub>3</sub> lattice and (b) a BaTiO<sub>3</sub>-NiO composite formation. The sintering temperature of BaTiO<sub>3</sub> is reported in literature to be ~  $1350^{\circ}$ C [8]. Intentionally the sintering temperature was kept lesser than this temperature to avoid preparing an entirely Ni doped BaTiO<sub>3</sub> sample. However, the double peaks representing the tetragonal nature seemed to converge thereby losing the tetragonality. Such a nature is generally the signature of doping. Hence, one shouldn't neglect such a possibility in these samples. Therefore, the phase percentage of both NiO and BaTiO<sub>3</sub> were estimated from Rietveld refinement. NiO is not present in S1, indicating the entire NiO being consumed by the BTO lattice, representing a complete doping. However, traces of NiO are observed in S2 (~1.57%) and S3 (4.63%). This clearly indicates that NiO is highly soluble in the BTO lattice with a solubility limit of ~10%. Hence, the composite system exists only in the S2 and S3 samples.

There is a possibility of Ni substituting either a B-site or an A-site or both of BTO in these samples. Note that the solid-state reaction between BTO and NiO is such that the ratio of Ba:Ti ions is 1:1. Substitution of any one ion will lead to the imbalance or shortage of the other, creating cationic defects. Such cationic defects are acceptable in lower doping percentages but are structurally less logical for higher (>2%) doping. Hence, most probably Ni was introduced to both the A-site and the B-site. In search of different possibilities, it was observed that there are reports for Ni-doped BTO (> 2%) with Ni replacing Ti at the B-site. Such replacements generally have been reported to trigger a hexagonal  $P6_3/mmc$  phase of BTO for Ni presence of ~2% [9]. On the other hand, there are other reports of Ni<sup>3+</sup>/Ni<sup>4+</sup>/Ni<sup>2+</sup> ions replacing Ba<sup>2+</sup> at the A-site. Such a

substitution instigates a non-centrosymmetric tetragonal to a more centrosymmetric cubic BTO (Fm-3m) structure[5]. Note that both Ni and Ti have 3d electrons in the outermost shells. Hence, it is more probable that Ni should be substituted for Ti. However, this should generate hexagonal phases. This was not observed in these samples. On the other hand, a loss of tetragonal phase in these samples is observed, which leads one to believe that Ni is substituting Ba in the modified BTO lattice. Therefore, this leads to a conflict in the validity or sustainability of the perovskite structure, leading to a considerable amount of B-site cationic deficit in the lattice. Hence, only one possibility remains which is the simultaneous substitution of the A-site and B-site, with the assumption that the hexagonal phase is deterred due to the reduction of tetragonality as a consequence of simultaneous A-site and B-site substitution.



Figure 2: (a) Rietveld measurement plots of the samples (b) BaTiO<sub>3</sub>(P4mm) (c) NiO (Fm-3m)

The crystal radius of Ba<sup>2+</sup> [XII] is 1.75 Å while that of Ti<sup>4+</sup>[VI] is 0.745 Å. The crystal radius of Ni is dependent on the valence state and the coordination of the ion. For an A-site substitution Ni should be XII-coordinated, while for a B-site substitution it should be VI-coordinated. From Shannon radii information Ni<sup>2+</sup> [VI] is ~0.83 Å, while Ni<sup>3+</sup>[VI] is ~0.7 Å for low spin state and 0.74 Å for high spin state. The lesser probable Ni<sup>4+</sup> [VI] is ~ 0.62 Å and can

have only a low spin state [10]. From these values one can observe that Ni<sup>2+</sup> is larger than the Ti<sup>4+</sup>. However, Ni<sup>3+</sup> seems to be more comparable with the Ti<sup>4+</sup>, whereas Ni<sup>4+</sup> is much smaller. The valence state of Ni in NiO is Ni<sup>2+</sup>. Hence, incorporation of such an ion is most probably going to generate a positive expansive pressure in the lattice. This expansive pressure might be the probable reason for a transformation to the hexagonal phase. However, Ni<sup>2+</sup> in a A-site should be XII-coordinated for which information is not available in the Shannon radii table. An approximation using the extrapolation of the values of IV, V, and VI-coordinated radii enables one to obtain a crystal radius of Ni<sup>2+</sup> [XII] of 1.1 Å to 1.27 Å, which is much less than the Ba<sup>2+</sup> ion. This type of substitution should in principle reduce the lattice constants. Indeed, such a reduction is observed in the cell volume for S1 and S2. Only in the case of S3 a nominal increase is observed, possibly due to a disproportionate distribution of Ni among the A-site and B-site.

Table 1: structural parameters obtained after Reitveld refinement									
(1-x) BTO-(x) NiO	a=b (Å)	С (Å)	BTO cell	Tetrago nality	Phase pe	rcentage			
			volume	(c/a)	BaTiO <sub>3</sub>	NiO			
<b>S0</b>	3.99565	4.03471	64.4152	1.0098	100	-			
<b>S1</b>	3.99890	4.02447	64.3560	1.0064	100	-			
S2	3.99806	4.02524	64.3414	1.0068	98.43	1.57			
\$3	3.99953	4.02453	64.3774	1.0063	95.37	4.63			



Figure 3: Variation in lattice parameter and c/a ratio with x

Rietveld refinement reveals a sharp reduction of both lattice parameters "a=b" and "c" with the incorporation of Ni in S1 and thereafter shows nominal changes in S2 and S3. Such a reduction generates a reduction in the cell volume and more importantly, the c/a ratio. The c/a ratio also follows the same trend as both parameters. This indicates that the "c" decreases more rapidly than the "a" parameter. Hence, there is a rapid reduction in the tetragonality of the samples with Ni doping.

#### Raman spectrum analysis:



Figure 4 : Raman spectrum of all samples

Raman spectroscopy is known to be a very sensitive tool in obtaining information about changes in the local symmetry of the structure. Any small changes in structure due to doping should be reflected in the Raman spectra better than any other technique. The Raman spectra of pure BTO powders reveal prominent peaks corresponding to the E(TO) phonon mode at ~40 cm<sup>-1</sup> (corresponding to TiO<sub>6</sub> octahedral distortion), an interference peak at ~80 cm<sup>-1</sup>, a broad A<sub>1</sub>(TO) mode at 275 cm<sup>-1</sup> ( the motion along the polar c axis of central Ti against the oxygen octahedron, bending vibration), a combined sharp B<sub>1</sub> mode (corresponding to out of phase vibrations of the adjacent basal oxygen atoms) and E(TO+LO) mode (corresponding to the displacements of the apical oxygens) at 307 cm<sup>-1</sup>, a combined A<sub>1</sub>(TO) mode (corresponding to O-Ti-O symmetric stretching TiO<sub>6</sub> oxygen octahedron) and E(TO) mode at ~520 cm<sup>-1</sup> and finally a combined A<sub>1</sub>(LO) and E(LO)

mode (corresponding to TiO<sub>6</sub> octahedral distortion) at 717 cm<sup>-1</sup> [11][12]. The nearby A1(TO) and the E(TO) modes ~ 520 cm<sup>-1</sup> appear to be convoluted and appear as a broad asymmetric peak. However, with doping this convolution reduces and these two can be visibly deconvoluted [13]. The peaks at 307 cm<sup>-1</sup>, 520 cm<sup>-1</sup>, and 717 cm<sup>-1</sup> arise due to the non-centrosymmetric of the TiO<sub>6</sub> octahedra and a signature of the tetragonality of the phase. Hence, a major tetragonal phase in all of these samples can be confirmed and is at par with the XRD data. There are no Raman peaks corresponding to the hexagonal phase seen in any of the samples. The intensity of the strongest peak at 307 cm<sup>-1</sup> is not altered significantly, indicating the presence of tetragonality in all the samples. The prominence of the  $A_1(TO)$  mode at ~540 cm<sup>-1</sup> in the S1, S2, S3 samples compared to S0 is correlated to the relative vibrations of the O-cage with the central Ti atom, thereby varying the polarity of the octahedron in the doped samples. This is valid proof of the presence of Ni at the Ti-site. The fact that Ni is also substituting Ba at the A-site can be revealed from the enhancement in the interference dip at 180 cm<sup>-1</sup> [interference due to A(TO)+A(LO)+E(LO)+E(TO)(corresponding to the out of phase vibration of Ba atoms and  $TiO_6$  octahedra)[12] and the broadness of the  $A_1(TO)$  mode at 275 cm<sup>-1</sup>. Ni at the A site has a weaker bonding with the basal O, thereby reducing the strength of the A-O bond, which is responsible for the distortion of the lattice in terms of the displacement of the O-cage away from the centrosymmetric position. The reduction of the intensity of these vibrations is a signature of the loss of the much-required distortions essential for ferroelectricity. Hence, these results are essential proof that the ferroelectricity in the doped materials has been compromised to some extent without absolutely losing it. The shifts in the Raman peaks observed for the prominent tetragonal peaks are tabulated in Table 2. One notable observation is the broadening of the most prominent E(TO) mode at 40 cm<sup>-1</sup>, A<sub>1</sub>(TO) mode at 275 cm<sup>-1</sup>, B<sub>1</sub>(TO+LO) mode at 307 cm<sup>-1</sup> along with the asymmetric broadband ~520 cm<sup>-1</sup>. This is a clear indication of the increasing positional disorder arising due to the presence of Ni in the BTO lattice [Ref].

Some modes appear like a weak hump at ~800 cm<sup>-1</sup>. Defects can generally induce disorder. Such disorder in the lattice sometimes leads to the violation of a few Raman selection rules, giving rise to new modes called Localized Vibrational Modes (LVM) [14]. Such a weak LVM may be visible at ~800 cm<sup>-1</sup> indicating the structural disorders. Note that for the S0 sample, these peaks are considerably weaker than S1, S2, and S3. This is also a proof of the breaking of the long-range ordering of ferroelectric material.

Table 2: Raman peak position								
(1-x)BTO- (x)NiO	E(TO)	A1(TO)	B1(TO)/E(L O/TO)	A1(TO)/E(T O)	A1(LO)/E(L O)			
SO	42.8225	275.52	307.994	518.041	717.424			
S1	44.114	268.006	307.994	515.62	717.424			
S2	42.8225	268.006	307.994	515.62	717.424			
S3	45.4052	266.752	307.994	515.62	717.424			

# SEM and EDX analysis:



Figure 5 : Field Emission Scanning Electron Microscopy(FESEM) Images of sintered pellets

SEM images of S1, S2 and S3 samples [Figure 5] reveal dense pellets with minimal porous nature. These samples are, therefore, perfect for DRA applications. The morphology of these samples revealed a combination of two different formations with two different size groups. Cuboid large grains of BTO-like phase were associated with spherical finer particles, most probably due to the NiO phase. However, for S0, proper sintering was not possible at 1250 °C, thereby revealing a porous surface. Hence, NiO plays an important role in reducing the sintering temperature.



Figure 6: Energy dispersive X-ray analysis

As the difference in percentage between the BTO-like phase and the NiO-like phase was maximum for the S3 sample, EDX mapping was done only for this sample. The sample revealed inhomogeneity of the constituent elements revealing specks of concentrated Ni-rich dots in the 2D maps of the samples. The homogeneity was obtained for the Ba, and Ti elements.



Figure 7: Elemental Mapping

# **Dielectric study:**

The complex permittivity,  $\varepsilon^*(\omega) = \varepsilon'(\omega) - i\varepsilon''(\omega)$ , where, the real  $\varepsilon'(\omega)$  part represents the energy storing capability of the material and the imaginary  $\varepsilon''(\omega)$  part represents the energy dissipation in the form of heat.  $\varepsilon'(\omega)$  is calculated with the following equation,  $\varepsilon'(\omega) = C_p d / \varepsilon_0 A$ , where  $C_p$ , d, A, and  $\varepsilon_0$  are the measured capacitance, thickness, area of the sample, dielectric constant of the free space respectively. The room temperature frequency-dependent permittivity and loss tangent is plotted in Fig:8.



Figure 8 : Room temperature (a) Dielectric constant (b) tan delta dispersion plot

For a DRA, the bandwidth is inversely proportional to a power of  $\epsilon_r$  [15]. Hence, a lower  $\epsilon_r$  should effectively widen the bandwidth, which is preferable for a wide-band signal transmission. On the other hand, the frequency of resonance is also inversely proportional to the square root of the  $\epsilon_r$  [1]. The Q factor of the antenna is inversely proportional to the tan $\delta$ . Hence, the bandwidth, which is also inversely proportional to the Q factor, should be proportional to tan $\delta$ . Hence, to optimize the situation, one needs to have an optimal dielectric constant ( $\epsilon_r$ ) ~20-80 in the GHz range, with low loss tangent (tan $\delta$ ) <0.01 [1]. The BTO-NiO mixture was chosen for this purpose enabling us to manipulate the  $\epsilon_r$  and tan $\delta$  in this GHz range. However, the experimental limitations allow us to measure only in the range 100 Hz to 1 MHz.

The dielectric constant of the samples depends mainly on four different contributions i.e., space charge polarization ( $\varepsilon_s$ ), dipolar polarization ( $\varepsilon_d$ ), ionic polarization ( $\varepsilon_i$ ), and electronic polarization ( $\varepsilon_e$ ). The response from electronic and ionic polarization becomes active at a frequency range of ~ 10<sup>16</sup> and 10<sup>13</sup> Hz, respectively. According to the Maxwell-Wagner interfacial polarization model, the contribution from space charge polarization remains effective below 100 KHz. At the higher frequencies, the dipoles cannot follow alteration of the applied ac electric field; thus, though at lower frequencies  $\varepsilon_s$ ,  $\varepsilon_i$ ,  $\varepsilon_d$ , and  $\varepsilon_e$  can contribute to  $\varepsilon'(\omega)$  at higher frequencies, only  $\varepsilon_e$  plays the role. This leads to a significant drop in dielectric constant at high-frequency range. The permittivity reduces drastically in the entire frequency range (100 Hz to 1 MHz) from S0 (1800 at 1kHz and 1700 at 1MHz) to the modified samples S1 (1000 at 1kHz and 900 at 1MHz), S2 (950 at 1kHz and 700 at 1MHz), and S3 (800 at 1kHz and 700 at 1MHz) [Figure 8]. Extrapolation of these results may give an approximate value of ~1500 at 1GHz for S0, considering no other contributions to  $\epsilon_r$  to be lessened (e.g. dipolar relaxation, etc.). However, the reported value of  $\epsilon_r$  of pure BTO is ~120 [ref]. This indicates the presence of at least one relaxation phenomena in between 1MHz and 1GHz. Thereby, the extrapolated values of the modified BTO samples in this study should also change accordingly. One can expect an  $\epsilon_r$  value <100 for S1, S2 and S3. The tanð increases considerably in the frequency range (1kHz to 100 kHz) for S0 (0.0479 at 1kHz and 0.01607 at 100 kHz) to the modified samples S1 (1.575 at 1kHz and 0.0343 at 100 kHz), and S2 (3.697 at 1kHz and 0.0891 at 100 kHz), and thereafter reduces for S3 (2.653 at 1kHz and 0.0483 at 100 kHz) [Figure 8].

With the incorporation of Ni in the BTO lattice there is a change of the lattice constitution, which seems to reduce  $\epsilon_r$  in S1 as compared to S0. In S2 one can observe a further reduction of  $\epsilon_r$ . Note that S2 contains ~1.5% of NiO. In S3  $\epsilon_r$  reduces further, with remnant NiO being ~4.5%. Assuming that the rest of the NiO has successfully infiltrated into the BTO lattice, substituting both Ba and Ti, one should expect major changes in the lattice with increasing Ni substitution. These changes should be reflected in the d-spacings of the BTO lattice. However, not much change is observed between the d-spacings of S1, S2 and S3, while,  $\epsilon_r$  reduces continuously for all frequencies. This indicates that although structurally there may not be a major change in the modified BTO lattice, the dielectric properties may have been affected. One effect that can be of relevance is the contribution of the NiO which forms the micro-regions in between the modified BTO grains. However, the permittivity of NiO is low enough to contribute drastically to this composite. Hence, most probably it is the simultaneous modification of the A-site and B-site that may be responsible for the reduction  $\epsilon_r$ .

The Universal Dielectric Response model (UDR) is used to analyze the polarization behavior of the dielectric material. According to the UDR model, the real part of the dielectric constant( $\varepsilon$ ') can be written as  $\varepsilon' = \tan(s\pi/2) \sigma_0 f^{s-1}/\varepsilon_0$  where 's' and ' $\sigma_0$ ' are frequency and temperature-dependent constants. In another form,  $\varepsilon'*f = A(T)*f^s$ , where  $A(T) = \tan(s\pi/2) \sigma_0/\varepsilon_0$  represents a temperature dependent parameter. Again, which is,  $\ln(\varepsilon'*f) = s*\ln(f) + \ln(A(T))$ , so the plot between  $\ln(f)$  vs.  $\ln(\varepsilon'*f)$  will have the slope equal to 's'. Fig.9 shows that all of the samples show a linear nature

throughout the experimental frequency region. The linear fitting gives s values. for S0, S1, S2 and S3 samples respectively. The value of 's' decreases from 0.993 (S0), to 0.979 (S1), and 0.953 (S2) revealing a decreasing polarization. Only for S3 the value of 's' (~0.976) shows a rising trend suggesting a better polarization in S3 than S2. Hence, from UDR analysis it appears that the S2 sample has least polarization.



Figure 9: Fitting plot for Universal Dielectric Model (UDM)

Thus, the properties analyzed for the BTO-NiO composite reveals that NiO incorporation reduces the sintering temperature with a prominent reduction in the permittivity and low loss tangent (<0.01). These properties make these samples suitable for DRA application in the C-Band range [4-8 GHz]. The design for a DRA antenna with a dielectric possessing the above properties and fitting the C-band criteria was optimized using HFSS. This is discussed in the following section.

#### **Dielectric resonator antenna (DRA) application**

Depending on the shape and size, a DRA can radiate at a certain resonating frequency. The radiation pattern of the antenna depends on the internal field distribution of the DRA. From the multipole analysis of the radiation pattern it can be shown that the most prominent contribution comes from the lower order terms e.g. electric dipole or magnetic dipole (oriented in different directions) along with less weightage from the other higher order terms (i.e. quadrupole, octupole)[15]. A very unique electro-magnetic field is generated at these frequencies, which are not confined within the resonator itself. These are called non-confined modes [16]. In order to resonate in a particular mode, the feeding mechanism should be decided specifically. In this work the DRA is fed with a microstrip line (MSL). This kind of coupling is efficient, simple, and easy to implement, where the DRA works like a finite waveguide placed on an open circuited transmission line. This truncated section of dielectric waveguide acts as a resonator by creating a standing wave pattern on excitation with EM wave[Ref;Kajfez, D. and A. A. Kishk. Dielectric resonator.]. All of these different parameters were optimized with the help of simulation and then used to fabricate the experimental design.

#### Simulation details:

The simulated antenna structure is shown in the fig:10. A cylindrical DR ( $r_{DRA}$ =5.72mm and  $h_{DRA}$ =2.25mm) is fed with a 50 $\Omega$  MSL of 35 mm (length) × 3 mm (width) fabricated on a FR4 substrate ( $\varepsilon_{subs}$ =4.4) with dimensions of 60 mm (length) × 60 mm (breadth) × 1.6mm (thickness). The same dimensions were maintained for the experimental work. The MSL was etched on one side of the FR4 substrate while the opposite conducting side was retained as the ground plate with the same dimensions as that of the substrate. These dimensions were maintained for this simulation, thereby maintaining parity between the theory and experiment.

The necessary condition  $\varepsilon_{subs} \ll \varepsilon_{DRA}$  helps to achieve an efficient coupling between the MSL and DRA [17]. Note that the  $\varepsilon_{DRA}$  value is an important input to this simulation. An appropriate value of  $\varepsilon_{DRA} \sim 30$  was needed to match the experimental minima at 7.28 GHz. Hence, as observed from the dielectric studies the value of  $\varepsilon_{r}$  is indeed much lesser than 100, as mentioned in the concluding remarks of the dielectric properties section. The width of the MSL is a very important parameter to match the impedance with the feed and so to the DRA, without which most of the signal will get reflected back. It is mainly decided by the height of the substrate and its dielectric constant [18]. The MSL is connected to a lumped port of 50 $\Omega$  to excite the DR. The height of this port is

equal to the substrate height (1.6mm) and the width is equal to the width of the MSL(3mm). A radiation box of air with size 120mm × 120mm × 50 mm is taken to calculate the far-field parameters. The dimension takes care of the fact that all the box surfaces are at least  $\lambda_0/4$  away from the radiating body ( $\lambda_0$  is the wavelength corresponding to the resonance frequency). The optimized values are obtained by varying different design parameters (length and width of MSL, substrate dimensions,  $r_{DRA}$ ,  $h_{DRA}$  and radiation box size) in the simulation. The optimum design parameters of the substrate, ground plane and microstrip line are tabulated in Table 3.

Table 3: Optimized design parameters (in mm)							
DRA radius (r <sub>DRA</sub> )	5.72	MSL width	3				
DRA hight (h <sub>DRA</sub> )	2.25	Substrate thickness	1.6				
MSL length	35	Substrate length $\times$ width	60 × 60				



Figure 10: (a) Simulated and (b) Fabricated DRA with microstripline (MSL)

# **Experimental Design:**

Three Cylindrical DRAs (CDRAs) were made from the S1, S2 and S3 samples. The CDRs were fabricated using a 13mm dia-set pellet maker. Sintering was performed as described in the methodology. The sintered CDRAs had dimensions of radius ( $r_{DRA}$ ) ~5.72 mm and height ( $h_{DRA}$ ) ~2.25 mm. The MSL is soldered to a compatible subminiature version A (SMA) connector. To ensure the relative positions of the DRA with respect to the MSL the entire substrate was marked with perpendicular lines 5mm apart. The S<sub>11</sub> parameter of the fabricated MSL was measured and

simulated to verify the authenticity of the design [Fig Sup1]. In the absence of DR, the EM waves create standing wave patterns by getting reflected back from the open end. The wavelengths of these standing waves are integral multiples of  $\lambda_0/\sqrt{\epsilon_{subs}}$ ; where  $\lambda_0$  is the operating wavelength [17]. After verifying the fabricated MSL the position of the DRA on MSL has been checked for maximum coupling.

#### Positioning the DRA:

A DR placed near to the MSL gets coupled to the magnetic field lines associated with it. The best way is to put the resonator symmetrically on top of the MSL about its length. It is reported that an asymmetric positioning can lead to less modal impurity with the presence of higher-order multi polar components[19][20]. The length up to which the open end of the MSL extends under the DRA, is called overlapping distance ( $l_0$ ). This is an important parameter to match the impedance and so the coupling between the DR and the MSL for a particular mode [21]. For higher values of dielectric constant (>20) it is easier to match the impedance. The benefit of MSL feeding is that the coupling can be made better by properly varying the  $l_0$ . In the present case the best coupling is obtained at  $l_0= 2.5$ mm. The most important parameter which helps to recognize the resonance is the S<sub>11</sub> parameter or the return loss. As most of the source energy gets transmitted and ultimately radiated via the DR, the S<sub>11</sub> parameter shows a distinguishing minima at the resonance frequencies.



Figure 12: (a) S<sub>11</sub> plots of all the samples. (b) Simulated and experimental S<sub>11</sub> plot of S<sub>3</sub> sample Figure 12(a) reveals the S<sub>11</sub> parameters of S1, S2 and S3. Note that the minima is significant (< -10dB) for all three samples with nearly the same resonating frequencies in the range 7 GHz to</p>

7.5 GHz. These observations indicate that given the dimensions of these DRAs being similar the dielectric properties should be similar too. Hence, although the simulation was performed on all three samples the S3 sample is being reported in this work.

The simulated and experimental return loss plots for S3 are shown in Fig:12 (b). This antenna achieved a simulated return loss of -18.73 dB at a frequency of 7.27 GHz and provided a 10-dB return loss bandwidth of 5.22%. Experimental results revealed a resonance at 7.282 GHz with return loss of -25.396 dB and bandwidth 10.01%. The mismatch between the simulated and experimental plots can be attributed to the air gap between the DRA and the substrate. As, in the simulated design the air gap was assumed to be zero.



Figure 13: Imaginary and Real part of Impedance

Fig. 13 represents the experimental real and imaginary part of impedance variation with frequency. Ideally at resonance, the real part has to be  $50\Omega$  with zero imaginary part (reactance). Experimentally, at 7.28 GHz it is 52.71- j4.81  $\Omega$ , representing a good impedance matching and coupling between the MSL and DRA. To understand the type of mode generated at resonant frequency the electric and magnetic field patterns needed to be analyzed as described in the modal analysis section.

#### Modal analysis:

The cylindrical DR offers three fundamental modes,  $\text{HEM}_{11\delta}$ ,  $\text{TM}_{01\delta}$  and  $\text{TE}_{01\delta}$  [22]. Here the first index denotes the number of full-period field variations in azimuthal direction, second one represents the no. of radial variations and the third index represents the variation in the zdirection[1]. For the TM<sub>01\delta</sub> and TE<sub>01\delta</sub> modes, the E field is radially outward and concentric circular about the axis respectively. That's why the field is independent of azimuthal variation and so the first index is zero. In the case of hybrid HEM<sub>11δ</sub> mode, the electric and magnetic fields have both transverse and longitudinal components. The radiation pattern of the HEM<sub>11δ</sub> mode looks ideally like a pattern of the half-wave dipole parallel to the ground plane [1]. It can be shown that if the  $\cos\theta$  term in the field expression is replaced by  $\sin\theta$  and vice versa or by a linear sum of them, it will still be a solution to Maxwell's equation. This azimuthal symmetry leads to a degeneracy in the system for which there are two orthogonal modes for HEM<sub>11δ</sub> mode at the same frequency [15].



Figure 14: E-Field at (a) Phase= $0^{\circ}$  and (b) Phase= $180^{\circ}$  within the DRA at HEM<sub>11 $\delta$ </sub> mode (top view inlet)

In order to analyze the mode generated, the electric and magnetic field patterns are simulated. The Fig. 14 and 15 shows the different field distributions at the resonant frequency (7.273 GHz). This distribution confirms that it was HEM<sub>11δ</sub>. This is the hybrid mode with lowest frequency [Kajfez, D. and A. A. Kishk. Dielectric resonator]. In the present case the dipole was placed in the X-Y plane, oscillating along the X-axis. The magnetic field was strongest in the equatorial plane, whereas the electric field was strongest at the top surface. The electric field lines curled around the magnetic field. The side view of the E-field at phase= $0^{\circ}$  (FIG. 14(a)) and phase=180° (FIG. 14(b))



revealed that the electric field vectors were getting directed in the opposite direction. From the top view, it is observable how the maximum field region is oscillating (denoted with red colored vectors) about the center.

# Figure 15: H-Field at (a) Phase=90° and (b) Phase=270° within the DRA at $HEM_{11\delta}$ mode (top view inlet)

Similar analysis can be inferred for H-field also. It is to be noted that the E-field and the H-field maximas are shifted by 90° phase difference in the time domain. The H field pattern at phase=90° (FIG. 15(a)) and at phase=270° [Fig;15(b)] are plotted.



Figure 15: (a) Gain and (b) Directivity plot

The resonance of the fabricated DRA is confirmed for resonating HEM<sub>11δ</sub> at 7.28 GHz. In order to analyze the efficiency of the antenna at the resonant frequency the gain and the directivity needs to be analyzed. The gain and directivity plots are shown in [Fig. 15 ]. The maximum gain obtained is 5.8 dB. It is observed that the proposed prototype is having an isotropic gain in the broadside direction in accordance with the HEM<sub>11δ</sub> mode [1]. The directivity plot has been shown in the E-plane ( $\emptyset$ =0° or X-Z plane) and the H-plane ( $\emptyset$ =90° or Y-Z plane). The back lobes are very weak.

#### Conclusion

A mixture of (1-x) BaTiO<sub>3</sub>-(x) NiO samples with x=0, 0.05, 0.10, 0.15 have been prepared through solid state sintering. The XRD results revealed a single tetragonal *P4mm* space group for x=0, and 0.05 indicating the complete incorporation of Ni in BTO lattice at the A-site and B-site. However, for x=0.10 and 0.15, a mixture of modified BTO and modified NiO composite has been formed.

The minority modified NiO phase is as low as 1.5% and 4.6% in x=0.10 and x=0.15 samples, respectively. From the modification of the XRD peaks and variation in the lattice parameters, the A-site, B- site doping of the Ni in BTO lattice, BTO-NiO composite formation are discussed. Raman spectroscopy analysis also confirms the XRD results of the modification in the lattice due to NiO incorporation. FE-SEM results show two types of morphology indicating the cuboid large grains of BTO-like phase associated with spherical finer particles due to the NiO phase. This was confirmed through 2D mapping. Dielectric studies revealed the reduction in the permittivity with increase in x by maintaining low tand value. The dielectric polarization of the materials was also analyzed using a Universal Dielectric Model (UDM) revealing the retention of the dipole moment in the material. These properties make these samples suitable for DRA application in the C-Band range [4-8 GHz]. The design for a DRA antenna with a dielectric possessing the above properties and fitting the C-band criteria was optimized using HFSS. The fabricated antenna achieved a simulated return loss of -18.73 dB at a frequency of 7.27 GHz and provided a 10-dB return loss bandwidth of 5.22%. Experimental results revealed a resonance at 7.282 GHz with return loss of -25.396 dB and bandwidth 10.01%. Modal analysis revealed that the generated mode is HEM<sub>11δ</sub> with maximum gain obtained of 5.8 dB with an isotropic gain in the broadside direction.

## Acknowledgement

MP would like to thank the Ministry of Education, Government of India, for the Prime Minister Research Fellowship (PMRF). Authors would like to acknowledge Sophisticated Instrumentation Facility, IIT Indore For the FE-SEM and Raman Spectroscopy measurement. The Authors would like to acknowledge the Department of Science and Technology (DST), Govt of India for providing the funds (DST/TDT/AMT/2017/200). The authors also acknowledge the Department of Science and Technology (DST), Govt. of India, for providing FIST instrumentation fund to the discipline of Physics, IIT Indore, to purchase a Raman Spectrometer (Grant Number SR/FST/PSI-225/2016).

#### References

- R. K. Mongia and P. Bhartia, "Dielectric resonator antennas—a review and general design relations for resonant frequency and bandwidth," *Int. J. Microw. Millim.-Wave Comput.-Aided Eng.*, vol. 4, no. 3, pp. 230–247, Jul. 1994, doi: 10.1002/mmce.4570040304.
- [2] B. Mukherjee, P. Patel, and J. Mukherjee, "A review of the recent advances in dielectric

resonator antennas," *J. Electromagn. Waves Appl.*, vol. 34, no. 9, pp. 1095–1158, Jun. 2020, doi: 10.1080/09205071.2020.1744484.

- [3] S. Long, M. McAllister, and Liang Shen, "The resonant cylindrical dielectric cavity antenna," *IEEE Trans. Antennas Propag.*, vol. 31, no. 3, pp. 406–412, May 1983, doi: 10.1109/TAP.1983.1143080.
- [4] M. Shehbaz, C. Du, D. Zhou, S. Xia, and Z. Xu, "Recent progress in dielectric resonator antenna: Materials, designs, fabrications, and their performance," *Appl. Phys. Rev.*, vol. 10, no. 2, p. 021303, Jun. 2023, doi: 10.1063/5.0128779.
- [5] C. Fu, N. Chen, and G. Du, "Comparative studies of nickel doping effects at A and B sites of BaTiO3 ceramics on their crystal structures and dielectric and ferroelectric properties," *Ceram. Int.*, vol. 43, no. 17, pp. 15927–15931, Dec. 2017, doi: 10.1016/j.ceramint.2017.08.169.
- [6] S. Lee, C. A. Randall, and Z. Liu, "Factors Limiting Equilibrium in Fabricating a Simple Ferroelectric Oxide: BaTiO 3," J. Am. Ceram. Soc., vol. 92, no. 1, pp. 222–228, Jan. 2009, doi: 10.1111/j.1551-2916.2008.02859.x.
- [7] K. Tsuzuku and M. Couzi, "In situ investigation of chemical reactions between BaCO3 and anatase or rutile TiO2," *J. Mater. Sci.*, vol. 47, no. 10, pp. 4481–4487, May 2012, doi: 10.1007/s10853-012-6310-9.
- [8] P. Maneesha *et al.*, "Effect of oxygen vacancies and cationic valence state on multiferroicity and magnetodielectric coupling in (1-x)BaTiO3.(x)LaFeO3 solid solution," *J. Alloys Compd.*, vol. 971, p. 172587, Jan. 2024, doi: 10.1016/j.jallcom.2023.172587.
- [9] S. K. Das, R. N. Mishra, and B. K. Roul, "Magnetic and ferroelectric properties of Ni doped BaTiO3," *Solid State Commun.*, vol. 191, pp. 19–24, Aug. 2014, doi: 10.1016/j.ssc.2014.04.001.
- [10] R. D. Shannon, "Revised effective ionic radii and systematic studies of interatomic distances in halides and chalcogenides," *Acta Crystallogr. Sect. A*, vol. 32, no. 5, pp. 751– 767, Sep. 1976, doi: 10.1107/S0567739476001551.
- [11] R. Amin, N. Khatun, and S. Sen, "Optimization of Pb content in enhancing ferroelectricity and shifting the Tc of BaTiO3 to a higher temperature," *J. Appl. Phys.*, vol. 126, no. 17, p. 174105, Nov. 2019, doi: 10.1063/1.5116651.
- [12] V. Dwij *et al.*, "Revisiting eigen displacements of tetragonal BaTiO3: Combined first principle and experimental investigation," *Phys. B Condens. Matter*, vol. 624, p. 413381, Jan. 2022, doi: 10.1016/j.physb.2021.413381.
- [13] S.-Y. Kuo, W.-Y. Liao, and W.-F. Hsieh, "Structural ordering transition and repulsion of the giant LO-TO splitting in polycrystalline Ba x Sr 1 – x TiO 3," *Phys. Rev. B*, vol. 64, no. 22, p. 224103, Nov. 2001, doi: 10.1103/PhysRevB.64.224103.
- [14] V. K. Veerapandiyan *et al.*, "B-site vacancy induced Raman scattering in BaTiO3-based ferroelectric ceramics," *J. Eur. Ceram. Soc.*, vol. 40, no. 13, pp. 4684–4688, Oct. 2020, doi: 10.1016/j.jeurceramsoc.2020.05.051.
- [15] B.-T. Lim, "Dielectric Resonator Antennas : theory and design," Massachusetts Institute of Technology, Department of Electrical Engineering and Computer Science, 1999. [Online]. Available: http://hdl.handle.net/1721.1/36782
- [16] R. Kumar Mongia and A. Ittipiboon, "Theoretical and experimental investigations on rectangular dielectric resonator antennas," *IEEE Trans. Antennas Propag.*, vol. 45, no. 9, pp. 1348–1356, Sep. 1997, doi: 10.1109/8.623123.
- [17] A. V. P. Kumar, V. Hamsakutty, J. Yohannan, and K. T. Mathew, "MICROSTRIPLINE

FED CYLINDRICAL DIELECTRIC RESONATOR ANTENNA WITH A COPLANAR PARASITIC STRIP," *Prog. Electromagn. Res.*, vol. 60, pp. 143–152, 2006, doi: 10.2528/PIER05121301.

- [18] C. A. Balanis, Ed., Modern Antenna Handbook, 1st ed. Wiley, 2008. doi: 10.1002/9780470294154.
- [19] A. K. Ojha and A. V. P. Kumar, "Tradeoffs in the feed point selection of a cylindrical dielectric resonator antenna," *Int. J. Microw. Wirel. Technol.*, vol. 10, no. 10, pp. 1196–1203, Dec. 2018, doi: 10.1017/S1759078718001095.
- [20] A. K. Ojha and A. V. P. Kumar, "The Role of Feed Perturbation in the Design of Microstrip-fed Cylindrical Dielectric Resonator Antennas," SSRN Electron. J., 2020, doi: 10.2139/ssrn.3572942.
- [21] R. A. Kranenburg and S. A. Long, "Microstrip transmission line excitation of dielectric resonator antennas," *Electron. Lett.*, vol. 24, no. 18, p. 1156, 1988, doi: 10.1049/el:19880785.
- [22] L. Zou, "Dielectric resonator antennas : from multifunction microwave devices to optical nano-antennas," The University of Adelaide, Australia, School of Electrical and Electronic Engineering, 2013. [Online]. Available: https://hdl.handle.net/2440/82146